

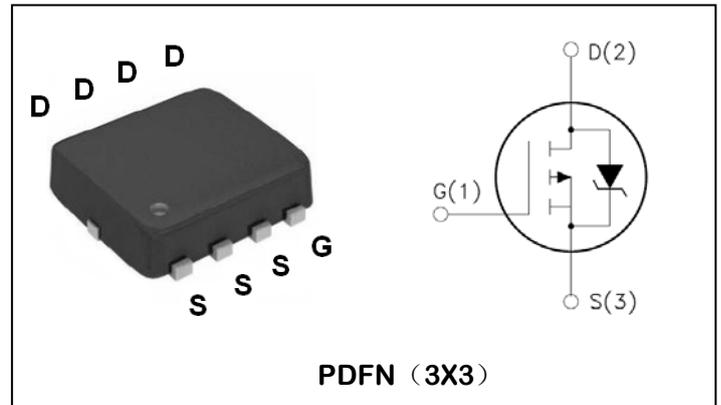
## P-Channel Logic Level Enhancement Mode Field Effect Transistor

### PRODUCT SUMMARY

$V_{DSS}$	$I_D$	$R_{DS(ON)}$ (m $\Omega$ )
-30V	-40A	10m $\Omega$

### Features:

- Low Gate Charge for Fast Switching Application
- Low  $R_{DS(ON)}$  to Minimize Conductive Loss
- Reliable and Rugged



### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise specified )

Symbol	Parameter		Ratings	Unit	
<b>Common Ratings</b>					
$V_{DSS}$	Drain-Source Voltage		-30	V	
$V_{GSS}$	Gate-Source Voltage		$\pm 20$		
$T_J$	Maximum Junction Temperature		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range		-55 to 150	$^\circ\text{C}$	
$I_S$	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$	-40	A	
<b>Mounted on Large Heat Sink</b>					
$I_{DM}$	300 $\mu\text{s}$ Pulse Drain Current Tested <sup>(2)</sup>		$T_C = 25^\circ\text{C}, V_{GS} = -10\text{V}$	-120	A
$I_D$	Continuous Drain Current <sup>(1)</sup>		$T_C = 25^\circ\text{C}, V_{GS} = -10\text{V}$	-40	A
			$T_C = 100^\circ\text{C}$ $V_{GS} = -10\text{V}$	-26	A
$P_D$	Maximum Power Dissipation		$T_C = 25^\circ\text{C}$	25.6	W

### Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{thJC}$	Thermal resistance junction-case max <sup>(1)</sup>	4.9	$^\circ\text{C/W}$
$R_{thJA}$	Thermal resistance junction-ambient max <sup>(1)</sup>	62	$^\circ\text{C/W}$

## Electrical Characteristics (TA=25°C Unless Otherwise Noted)

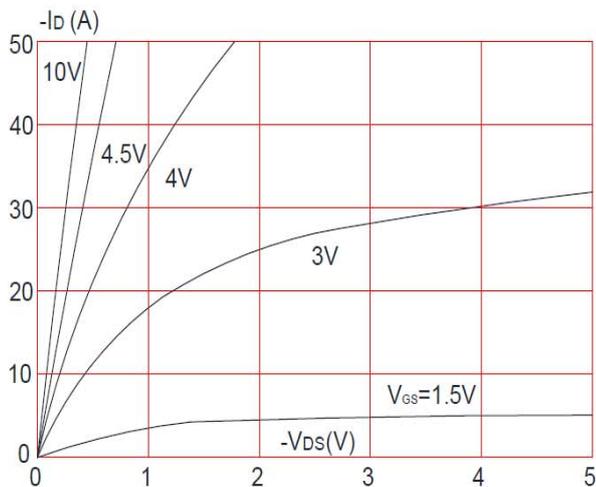
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>On/off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250uA	-30	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -27V, V <sub>GS</sub> =0V T <sub>J</sub> =25°C	--	--	-1	uA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250uA	-1.0	-1.6	-2.5	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
R <sub>DS(ON)</sub>	Drain-Source On-state Resistance <sup>(2)</sup>	V <sub>GS</sub> = -10V, I <sub>DS</sub> =-20A	--	7.5	10	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>DS</sub> =-10A	--	11.6	16	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> = -15V, Frequency=1.0MHz	--	3564	--	pF
C <sub>oss</sub>	Output Capacitance					
C <sub>rss</sub>	Reverse Transfer Capacitance					
<b>Switching Characteristics</b>						
t <sub>d(ON)</sub>	Turn-on Delay Time <sup>(1)</sup>	V <sub>DD</sub> =-15V, I <sub>D</sub> = -20A, V <sub>GS</sub> = -10V, R <sub>GEN</sub> =2.5 Ω	--	16	--	ns
t <sub>r</sub>	Turn-on Rise Time <sup>(1)</sup>					
t <sub>d(OFF)</sub>	Turn-off Delay Time <sup>(1)</sup>					
t <sub>f</sub>	Turn-off Fall Time <sup>(1)</sup>					
Q <sub>g</sub>	Total Gate Charge <sup>(1)</sup>	V <sub>DS</sub> =-15V, V <sub>GS</sub> = -10V, I <sub>DS</sub> =-20A	--	37	--	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>(1)</sup>					
Q <sub>gd</sub>	Gate-Drain Charge <sup>(1)</sup>					
<b>Avalanche Characteristics</b>						
EAS	Single Pulse Avalanche Energy <sup>(3)</sup>	V <sub>DD</sub> =-15V, L=0.5mH, V <sub>GS</sub> =1 0V, R <sub>g</sub> =25 Ω, V <sub>GS</sub> =-10V	121	--	--	mJ
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage <sup>(2)</sup>	I <sub>SD</sub> =-30A, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	--	-0.8	-1.2	V

### NOTES:

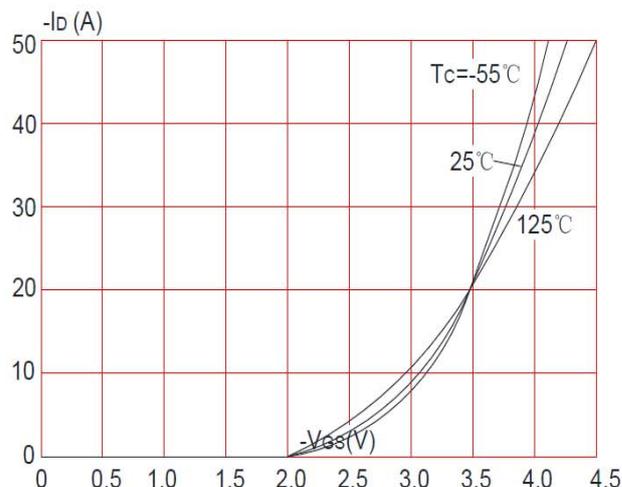
1. Surface Mounted on FR4 Board, t ≤ 10 sec.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The Min. value is 100% EAS tested guarantee.

## Typical Performance Characteristics

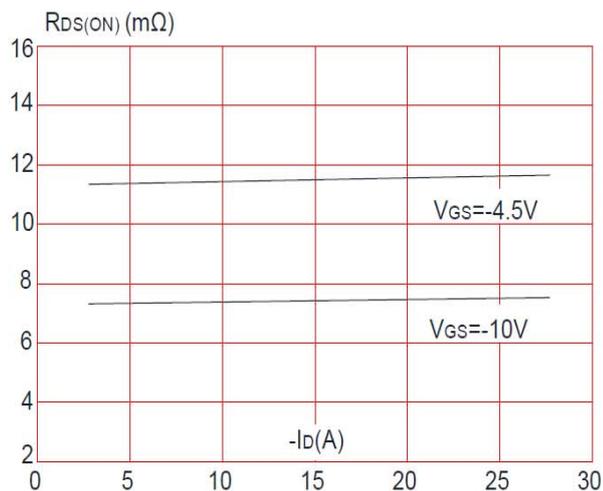
**Figure 1: Output Characteristics**



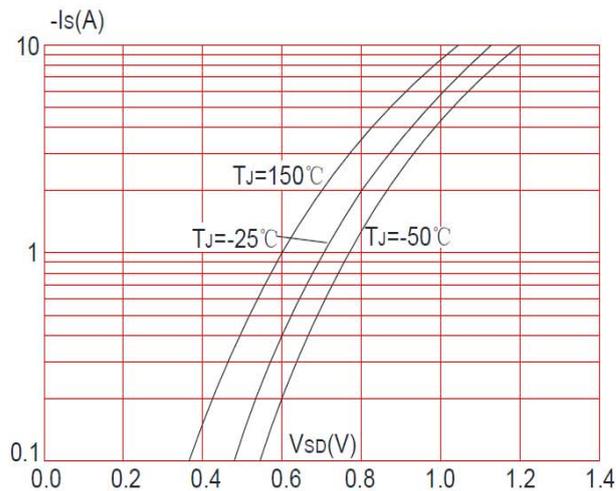
**Figure 2: Typical Transfer Characteristics**



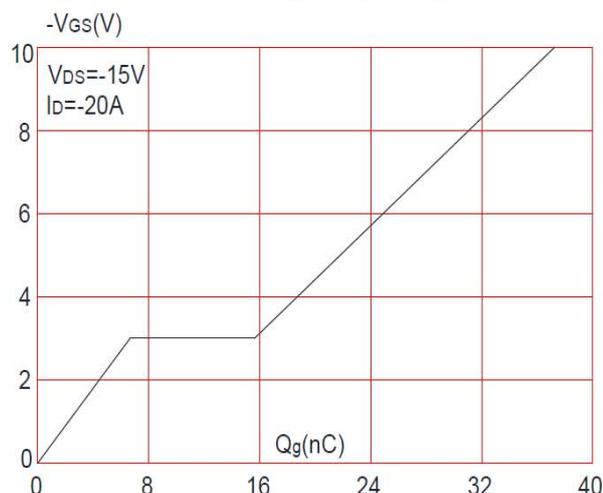
**Figure 3: On-resistance vs. Drain Current**



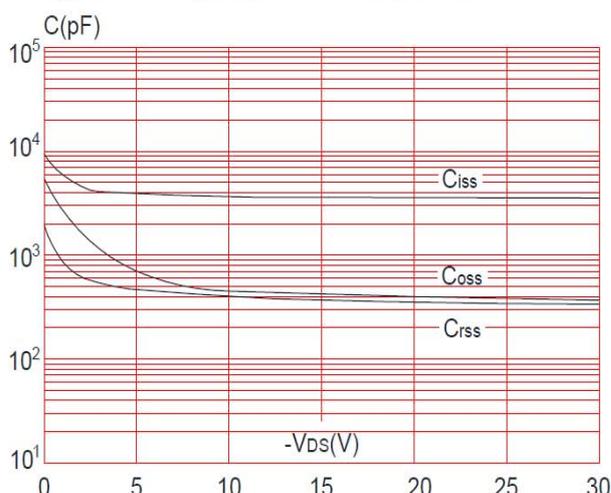
**Figure 4: Body Diode Characteristics**



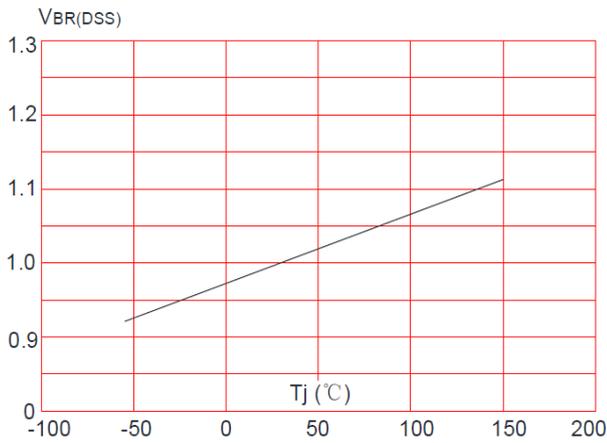
**Figure 5: Gate Charge Characteristics**



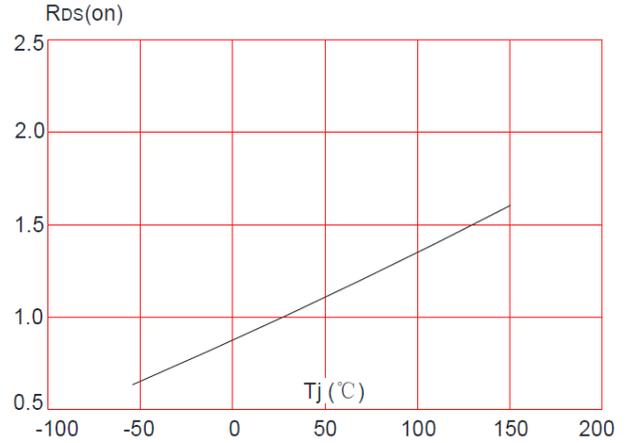
**Figure 6: Capacitance Characteristics**



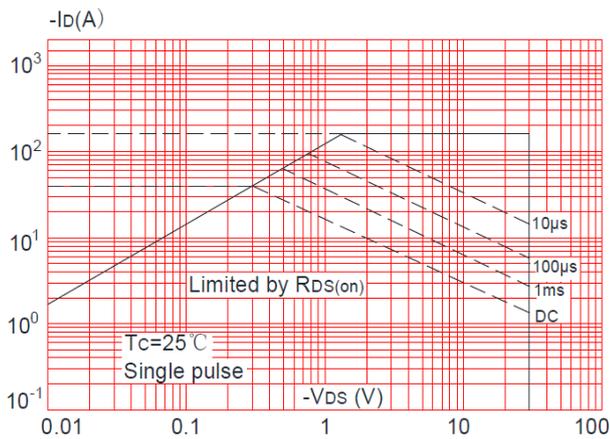
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



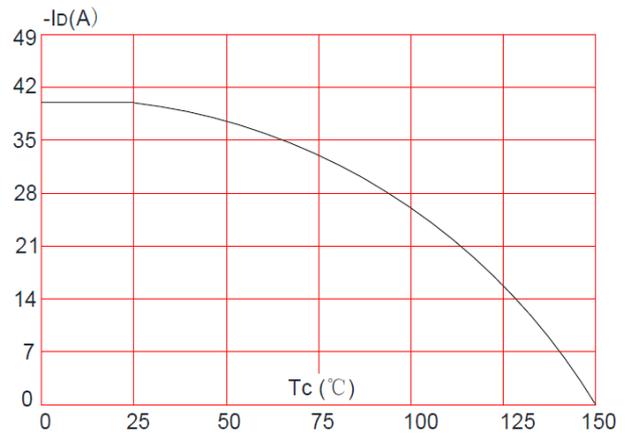
**Figure 8: Normalized on Resistance vs. Junction Temperature**



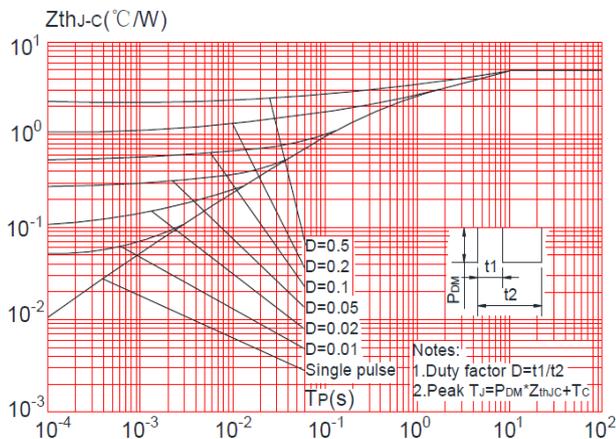
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**

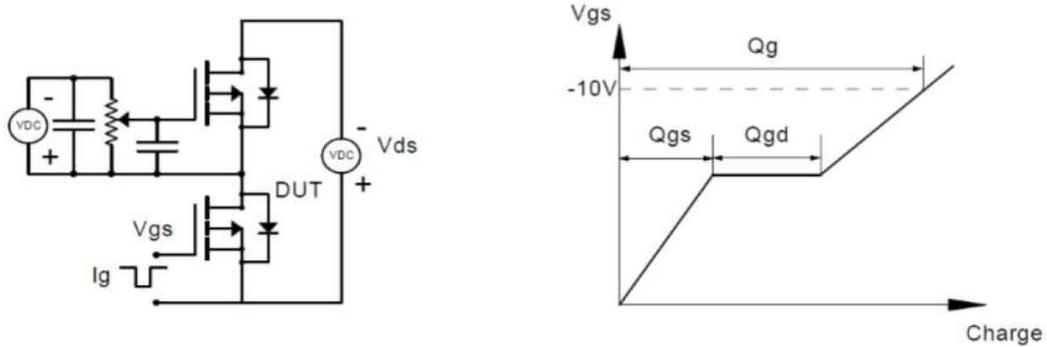


**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**

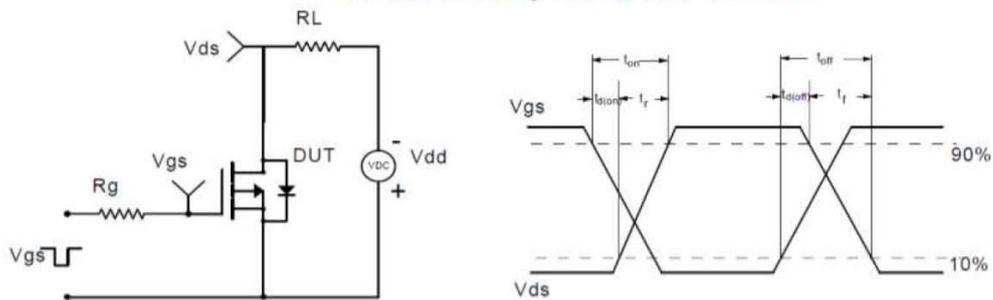


## Test Circuit

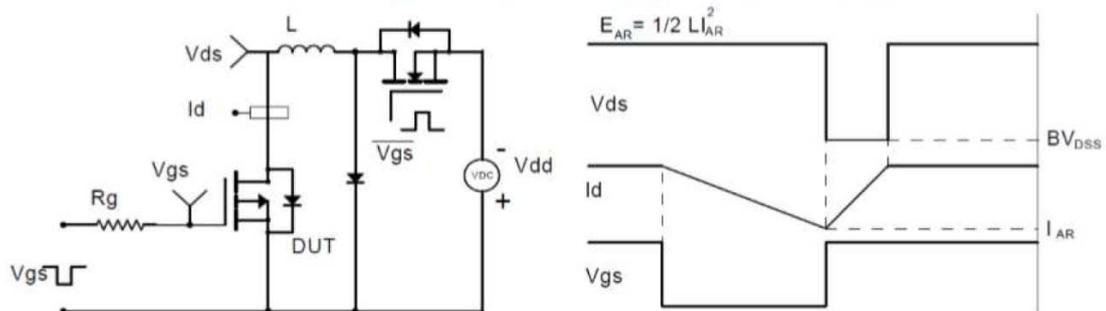
Gate Charge Test Circuit & Waveform



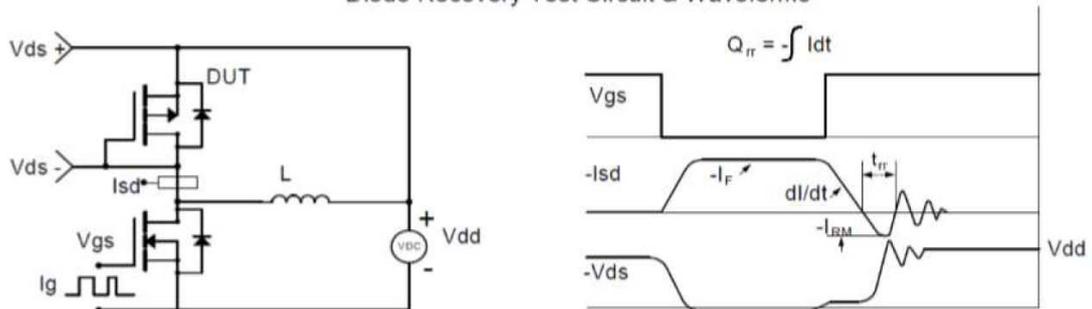
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms





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